

HD74HC367

Hex Bus Drivers (Noninverted Data Outputs with 3-state outputs)

REJ03D0617-0200
 (Previous ADE-205-496)
 Rev.2.00
 Jan 31, 2006

Features

- High Speed Operation: t_{pd} (A to Y) = 8.5 ns typ ($C_L = 50$ pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2$ to 6 V
- Low Input Current: 1 μ A max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max ($T_a = 25^\circ\text{C}$)
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC367P	DILP-16 pin	PRDP0016AE-B (DP-16FV)	P	—
HD74HC367FPEL	SOP-16 pin (JEITA)	PRSP0016DH-B (FP-16DAV)	FP	EL (2,000 pcs/reel)
HD74HC367RPEL	SOP-16 pin (JEDEC)	PRSP0016DG-A (FP-16DNV)	RP	EL (2,500 pcs/reel)

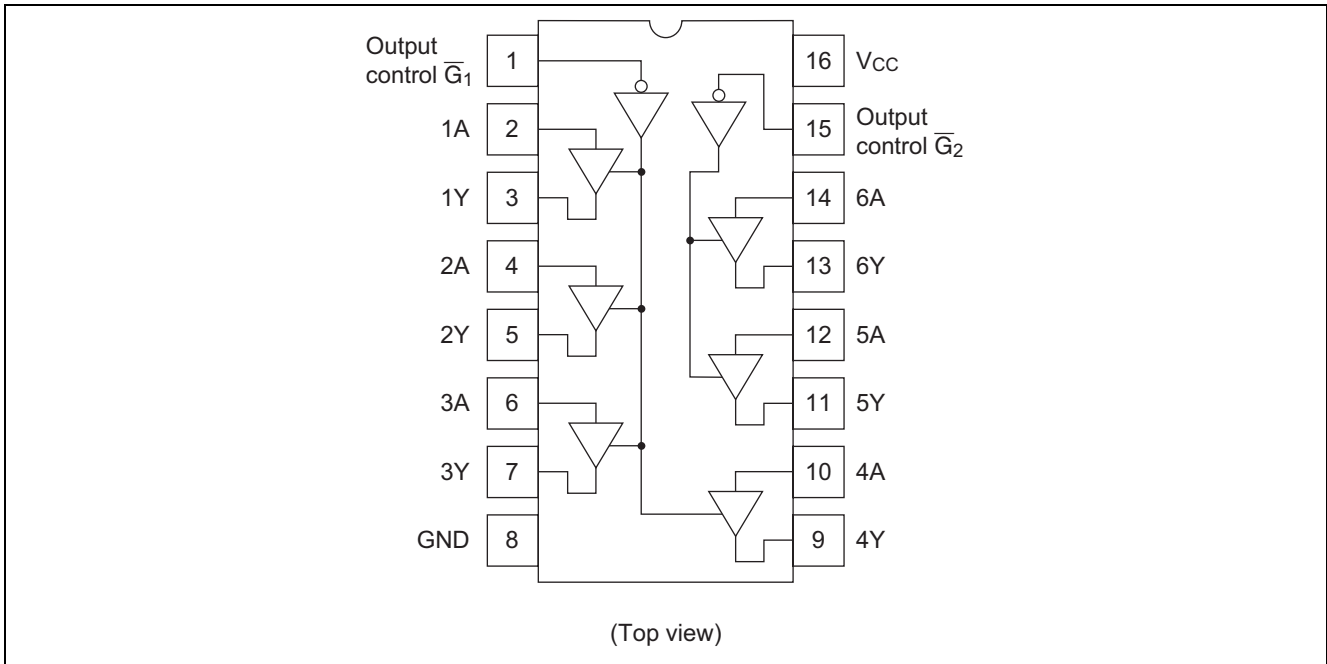
Note: Please consult the sales office for the above package availability.

Function Table

Inputs		Output
\bar{G}	A	Y
H	X	Z
L	L	L
L	H	H

Notes: 1. H; High level, L; Low level, X; Irrelevant, Z; High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage range	V_{CC}	-0.5 to 7.0	V
Input / Output voltage	V_{IN}, V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
Input / Output diode current	I_{IK}, I_{OK}	± 20	mA
Output current	I_{OUT}	± 35	mA
V_{CC}, GND current	I_{CC} or I_{GND}	± 75	mA
Power dissipation	P_T	500	mW
Storage temperature	T_{stg}	-65 to +150	$^{\circ}C$

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	2 to 6	V	
Input / Output voltage	V_{IN}, V_{OUT}	0 to V_{CC}	V	
Operating temperature	T_a	-40 to 85	$^{\circ}C$	
Input rise / fall time ^{*1}	t_r, t_f	0 to 1000	ns	$V_{CC} = 2.0 V$
		0 to 500		$V_{CC} = 4.5 V$
		0 to 400		$V_{CC} = 6.0 V$

Notes: 1. This item guarantees maximum limit when one input switches.
 Waveform: Refer to test circuit of switching characteristics.

Electrical Characteristics

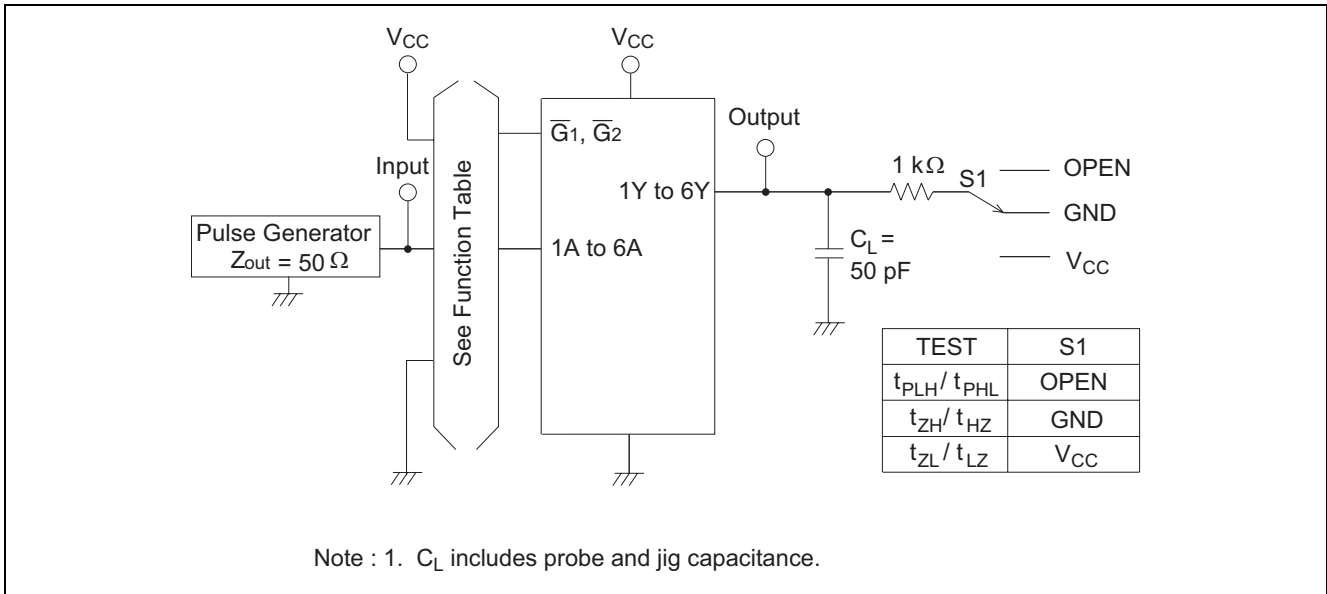
Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions		
			Min	Typ	Max	Min	Max				
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V			
		4.5	3.15	—	—	3.15	—				
		6.0	4.2	—	—	4.2	—				
	V _{IL}	2.0	—	—	0.5	—	0.5	V			
		4.5	—	—	1.35	—	1.35				
		6.0	—	—	1.8	—	1.8				
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V _{IH} or V _{IL}	I _{OH} = -20 μA	
		4.5	4.4	4.5	—	4.4	—			I _{OH} = -6 mA	
		6.0	5.9	6.0	—	5.9	—			I _{OH} = -7.8 mA	
		4.5	4.18	—	—	4.13	—				
		6.0	5.68	—	—	5.63	—				
	V _{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V _{IH} or V _{IL}	I _{OL} = 20 μA	
		4.5	—	0.0	0.1	—	0.1				
		6.0	—	0.0	0.1	—	0.1				
		4.5	—	—	0.26	—	0.33			I _{OH} = 6 mA	
		6.0	—	—	0.26	—	0.33			I _{OH} = 7.8 mA	
Off-state output current	I _{oz}	6.0	—	—	±0.5	—	±5.0	μA	Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND		
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	μA	Vin = V _{CC} or GND		
Quiescent supply current	I _{CC}	6.0	—	—	4.0	—	40	μA	Vin = V _{CC} or GND, Iout = 0 μA		

Switching Characteristics

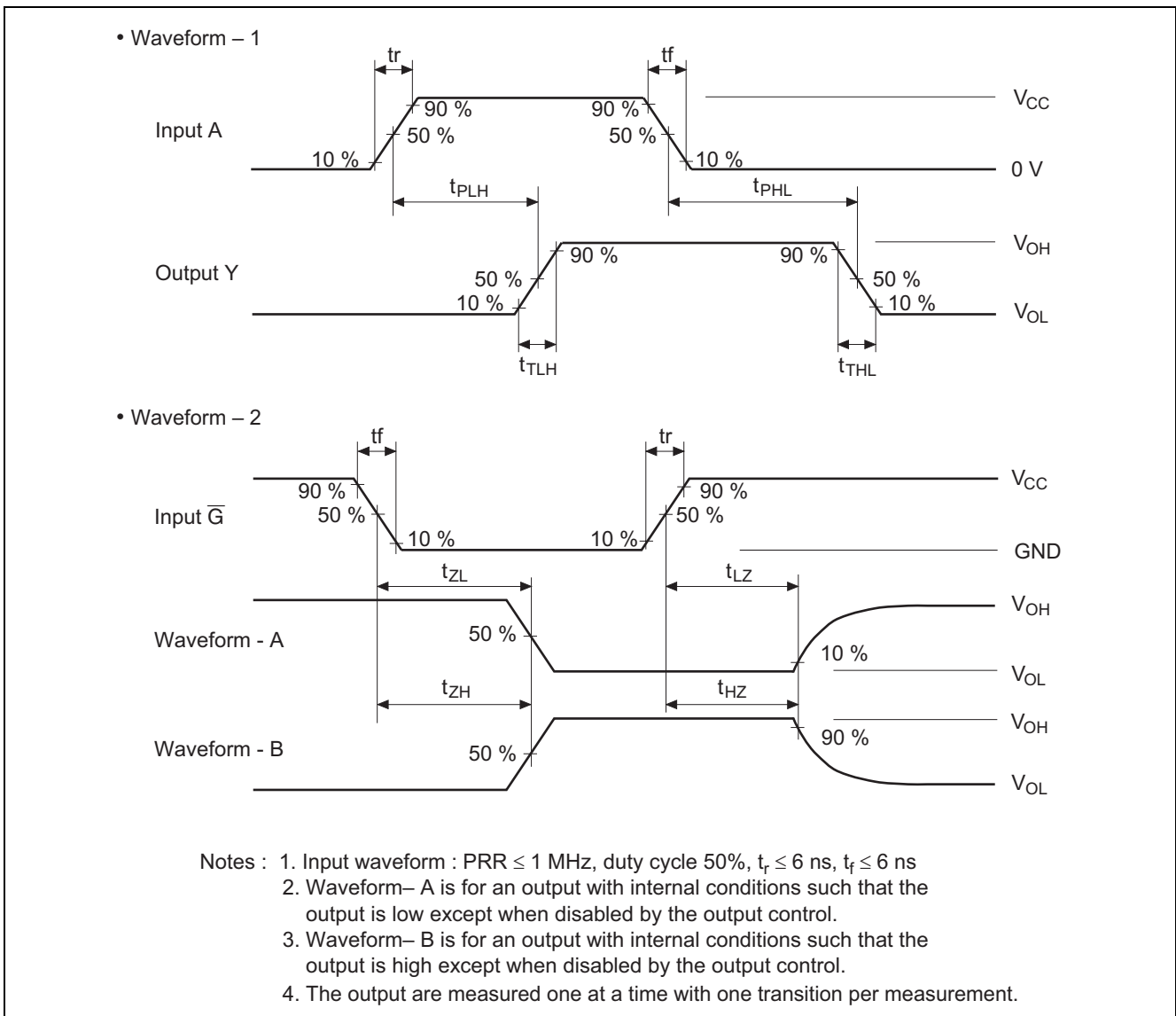
(C_L = 50 pF, Input t_r = t_f = 6 ns)

Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Propagation delay time	t _{PLH}	2.0	—	—	120	—	150	ns		
	t _{PHL}	4.5	—	9	24	—	30			
		6.0	—	—	20	—	26			
Output enable time	t _{ZH}	2.0	—	—	190	—	240	ns		
	t _{ZL}	4.5	—	12	38	—	48			
		6.0	—	—	32	—	41			
Output disable time	t _{HZ}	2.0	—	—	175	—	220	ns		
	t _{LZ}	4.5	—	15	35	—	44			
		6.0	—	—	30	—	37			
Output rise/fall time	t _{TLH}	2.0	—	—	60	—	75	ns		
	t _{THL}	4.5	—	4	12	—	15			
		6.0	—	—	10	—	13			
Input capacitance	C _{in}	—	—	5	10	—	10	pF		

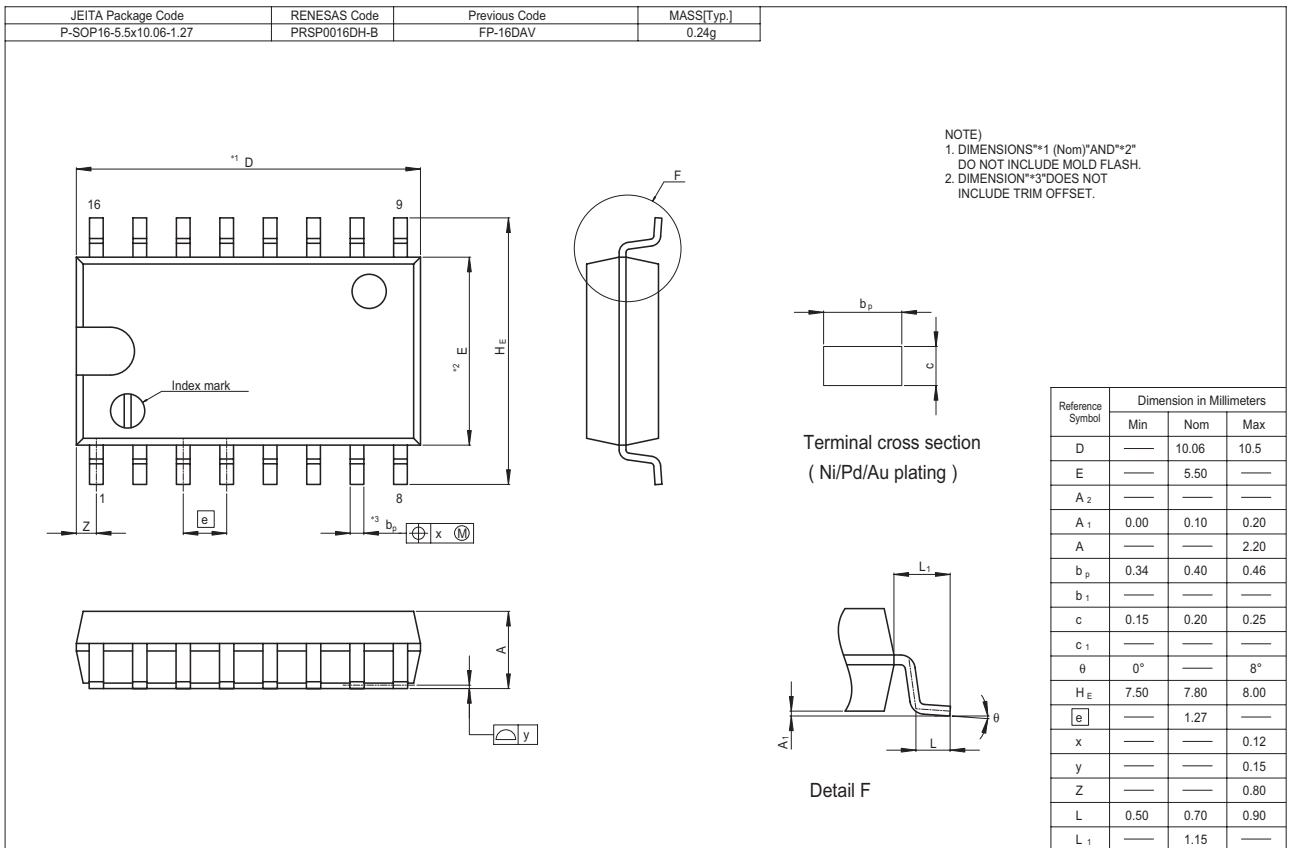
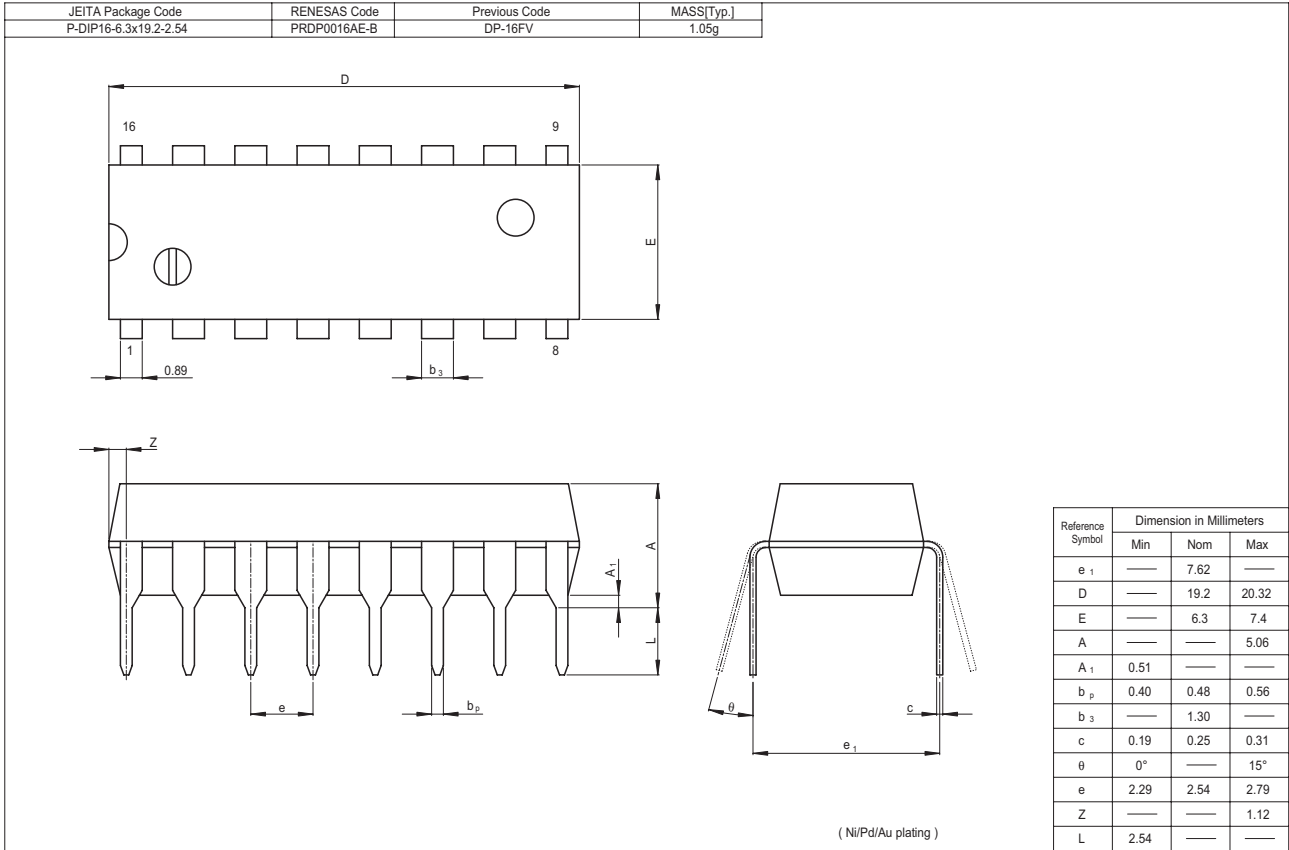
Test Circuit



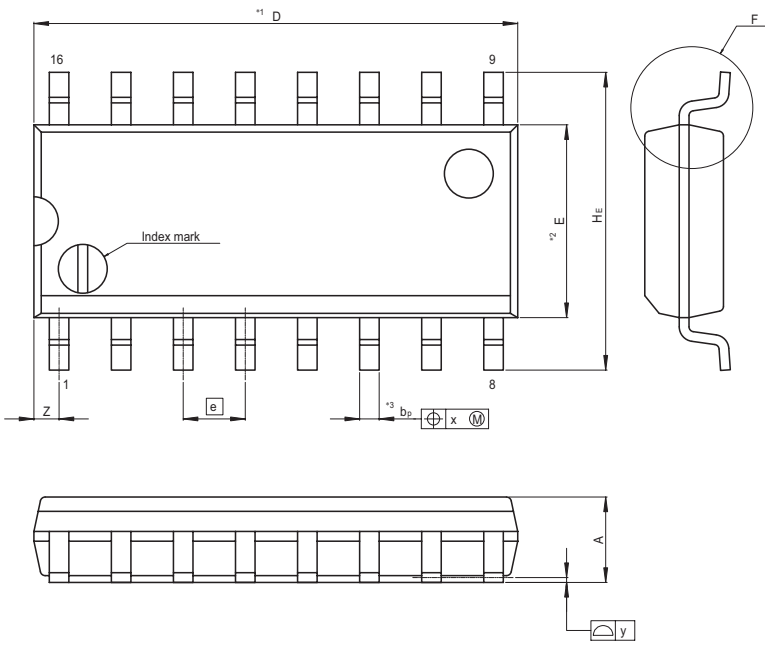
Waveforms



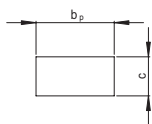
Package Dimensions



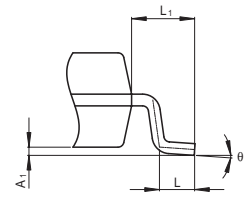
JEITA Package Code P-SOP16-3.95x9.9-1.27	RENESAS Code PRSP0016DG-A	Previous Code FP-16DNV	MASS[Typ.] 0.15g
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NOTE)
1. DIMENSIONS**1 (Nom)**AND**2*
DO NOT INCLUDE MOLD FLASH.
2. DIMENSION**3*DOES NOT
INCLUDE TRIM OFFSET.



Terminal cross section
(Ni/Pd/Au plating)



Detail F

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	9.90	10.30
E	—	3.95	—
A ₂	—	—	—
A ₁	0.10	0.14	0.25
A	—	—	1.75
b _p	0.34	0.40	0.46
b ₁	—	—	—
c	0.15	0.20	0.25
c ₁	—	—	—
θ	0°	—	8°
H _E	5.80	6.10	6.20
e	—	1.27	—
x	—	—	0.25
y	—	—	0.15
Z	—	—	0.635
L	0.40	0.60	1.27
L ₁	—	1.08	—

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